



P-CHANNEL ENHANCEMENT MODE MOSFET

Features

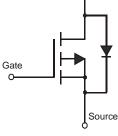
- Low On-Resistance:
 - $R_{DS(ON)} < 120m\Omega @ V_{GS} = -4.5V$ $R_{DS(ON)} < 240 m\Omega @ V_{GS} = -2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



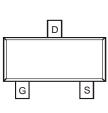
Top View



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Drain

Equivalent Circuit



Top View

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V _{DSS}	-30	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 1)	T _A = 25°C T _A = 70°C	I _D	-2.8 -2.2	A
Drain Current (Note 1)	Pulsed	I _{DM}	-9	A
Body-Diode Continuous Current (Note 1)		Is	-2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	1.4	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 1)	$R_{ ext{ heta}JA}$	90	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

1. Device mounted on FR-4 PCB. t \leq 5 sec. Notes:

2. No purposefully added lead.

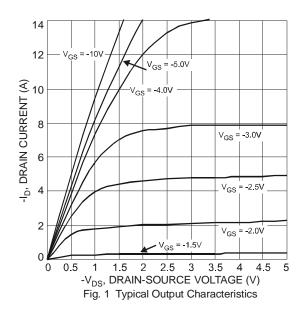
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

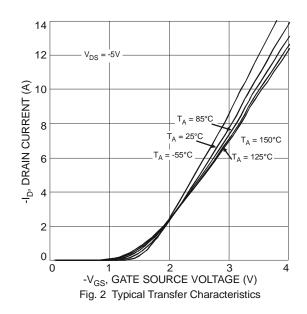


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)	·						
Gate Threshold Voltage	V _{GS(th)}	-0.6	_	-1.4	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		_	_	120	mΩ	V _{GS} = -4.5V, I _D = -2.8A	
Static Dialit-Source Off-Resistance	R _{DS (ON)}	_		240	1115.2	$V_{GS} = -2.5V, I_D = -1.8A$	
Forward Transconductance	g fs	_	5	_	S	$V_{DS} = -5V, I_D = -2.8A$	
Source-Drain Diode Forward Voltage	V _{SD}	_	_	-1.1	V	$V_{GS} = 0V, I_{S} = -2.0A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}		285	—	pF		
Output Capacitance	Coss		56	_	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	40	_	pF		
Gate Resistance	R _G		13	_	Ω	$V_{DS} = 0V, V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS	·						
Turn-On Delay Time	t _{d(on)}		5.6	_			
Rise Time	tr	_	6.8	_		V _{DS} = -15V, V _{GS} = -4.5V,	
Turn-Off Delay Time	t _{d(off)}	_	35.3	_	ns	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t _f	_	19.2	_			
Total Gate Charge	Q _G	_	6.7 3.0	_		$V_{DS} = -15V, V_{GS} = -10V, I_D = -1.0A$	
Gate-Source Charge	Q _{GS}	_	0.8	_	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -1.0A	
Gate-Drain Charge	Q _{GD}	_	0.5	_	1		

Notes: 4. Short duration pulse test used to minimize self-heating effect.



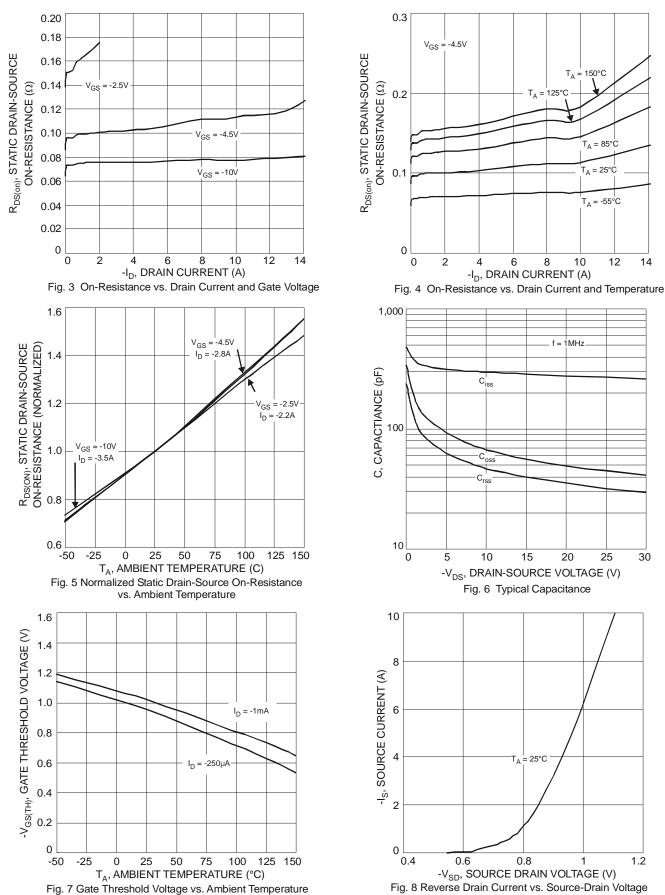






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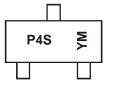


Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3120L-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

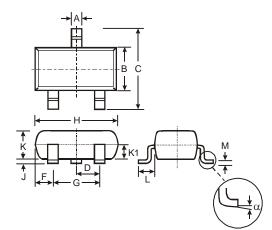


 $\begin{array}{l} \mathsf{P4S} = \mathsf{Product Type Marking Code} \\ \mathsf{YM} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex:} \ \mathsf{V} = 2008) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex:} \ 9 = \mathsf{September}) \end{array}$

Date Code Key

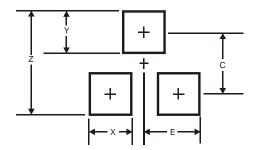
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



	SOT-23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
ĸ	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
С	2.0
E	1.35



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